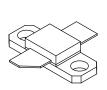
The RF Line NPN Silicon RF Power Transistor

Designed for 28 Volt microwave large-signal, common base, Class-C CW amplifier applications in the range 1600 – 1640 MHz.

- Specified 28 Volt, 1.6 GHz Class–C Characteristics
 Output Power = 30 Watts
 Minimum Gain = 7.5 dB, @ 30 Watts
 Minimum Efficiency = 40% @ 30 Watts
- Characterized with Series Equivalent Large–Signal Parameters from 1500 MHz to 1700 MHz
- · Silicon Nitride Passivated
- Gold Metallized, Emitter Ballasted for Long Life and Resistance to Metal Migration
- Circuit board photomaster available upon request by contacting RF Tactical Marketing in Phoenix, AZ.

MRF16030

30 WATTS, 1.6 GHz RF POWER TRANSISTOR NPN SILICON



CASE 395C-01, STYLE 2

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V _{CES}	60	Vdc
Emitter–Base Voltage	VEBO	4.0	Vdc
Collector-Current	IC	4.0	Adc
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	103 0.58	Watts °C/W
Storage Temperature Range	T _{stg}	-65 to +150	°C

THERMAL CHARACTERISTICS

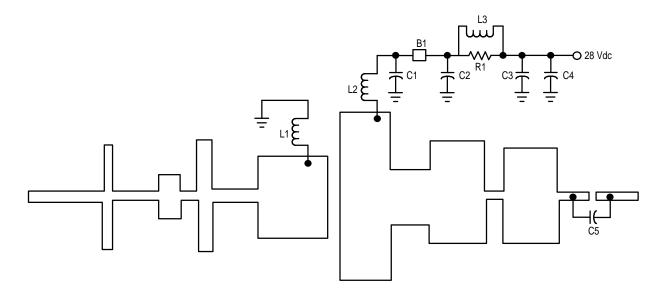
_				
	Thermal Resistance — Junction to Case (1) (2)	$R_{ heta JC}$	1.7	°C/W

⁽¹⁾ Thermal measurement performed using CW RF operating condition.

⁽²⁾ Thermal resistance is determined under specified RF operating conditions by infrared measurement techniques.

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

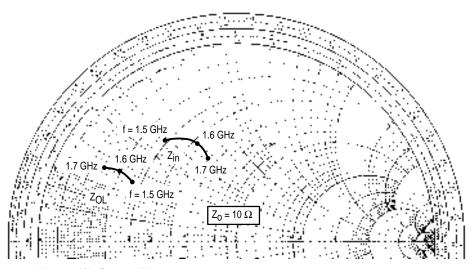
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS				•	•
Collector–Emitter Breakdown Voltage (I _C = 100 mAdc, V _{BE} = 0)	V(BR)CES	55	_	_	Vdc
Collector–Base Breakdown Voltage (I _C = 100 mAdc, I _E = 0)	V(BR)CBO	55	_	_	Vdc
Emitter–Base Breakdown Voltage $(I_E = 10 \text{ mAdc}, I_C = 0)$	V(BR)EBO	4.0	_	_	Vdc
Collector Cutoff Current (V _{CE} = 28 Vdc, V _{BE} = 0)	ICES	_	_	10	mAdc
ON CHARACTERISTICS			•	•	•
DC Current Gain (I _{CE} = 1.0 Adc, V _{CE} = 5.0 Vdc)	hFE	20	35	80	_
FUNCTIONAL TESTS			•	•	•
Collector–Base Amplifier Power Gain (V _{CC} = 28 Vdc, P _{Out} = 30 Watts, f = 1600/1640 MHz)	G _{pe}	7.5	7.7	_	dB
Collector Efficiency (V _{CC} = 28 Vdc, P _{out} = 30 Watts, f = 1600/1640 MHz)	η	40	45	_	%
Input Return Loss (V _{CC} = 28 Vdc, P _{out} = 30 Watts, f = 1600/1640 MHz)	I _{RL}	8.0	_	_	dB
Output Mismatch Stress V _{CC} = 28 Vdc, P _{out} = 30 Watts, f = 1600 MHz, Load VSWR = 3:1, All phase angles at frequency of test	Ψ	No Degradation in Output Power			



Board Material – Teflon® Glass Laminate Dielectric Thickness = 0.30", ϵ_Γ = 2.55", 2.0 oz. Copper

B1	Fair Rite Bead on #24 Wire	C4	47 μF, 50 V, Electrolytic
C1, C5	100 pF, B Case, ATC Chip Cap	L1, L2	3 Turns, #18, 0.133" ID, 0.15" Long
C2	0.1 μF, Dipped Mica Cap	L3	9 Turns, #24 Enamel
C3	0.1 μF, Chip Cap	R1	82 Ω, 1.0 W, Carbon

Figure 1. MRF16030 Test Fixture Schematic



 V_{CC} = 28 Vdc, P_{out} = 30 W

f MHz	Z _{in} Ohms	Z _{OL} * Ohms
1500	3.05 + j 4.88	2.66 + j 2.53
1600	4.32 + j 6.00	1.79 + j 2.80
1700	5.62 + j 5.79	1.51 + j 2.64

 Z_{OL}^* = Conjugate of the optimum load impedance into which the device output operates at a given output power, voltage and frequency.

NOTE: Input and output impedance values given are measured from gate to gate and drain to drain respectively.

Figure 2. Series Equivalent Input/Output Impedance

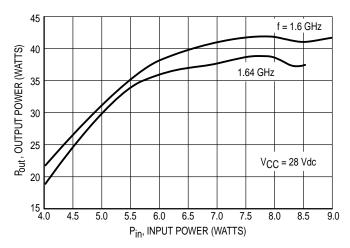
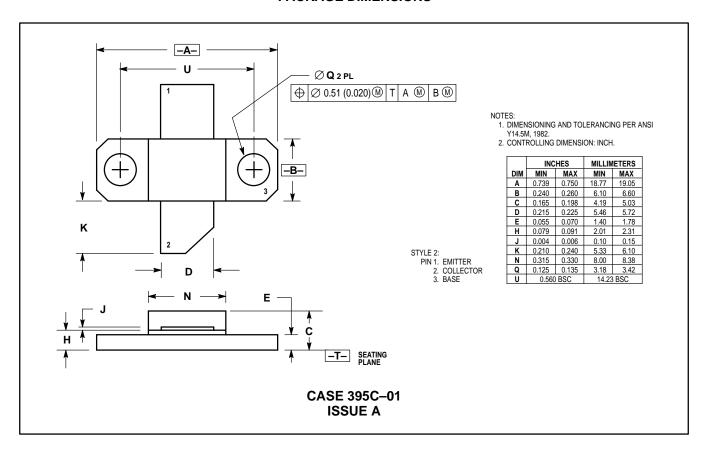


Figure 3. Output Power versus Input Power

PACKAGE DIMENSIONS



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How to reach us:

USA/EUROPE: Motorola Literature Distribution; P.O. Box 20912; Phoenix, Arizona 85036. 1–800–441–2447

MFAX: RMFAX0@email.sps.mot.com – TOUCHTONE (602) 244–6609 INTERNET: http://Design_NET.com

JAPAN: Nippon Motorola Ltd.; Tatsumi–SPD–JLDC, Toshikatsu Otsuki, 6F Seibu–Butsuryu–Center, 3–14–2 Tatsumi Koto–Ku, Tokyo 135, Japan. 03–3521–8315

HONG KONG: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park, 51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852–26629298



